NL27WZ16

Dual Buffer

The NL27WZ16 is a high performance dual buffer operating from a 1.65 to 5.5 V supply. At V_{CC} = 3 V, high impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance.

Features

- Extremely High Speed: t_{PD} 2.0 ns (typical) at V_{CC} = 5 V
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs
- LVTTL Compatible − Interface Capability With 5 V TTL Logic with V_{CC} = 3 V
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 72; Equivalent Gate = 18
- These Devices are Pb−Free and are RoHS Compliant
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable

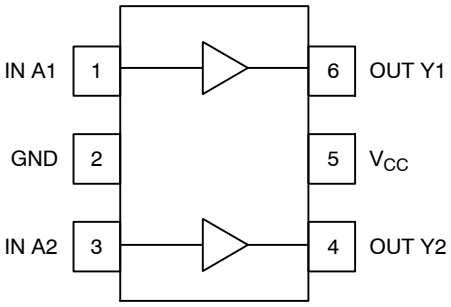


Figure 1. Pinout (Top View)

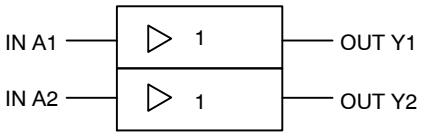


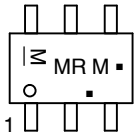
Figure 2. Logic Symbol

ON Semiconductor®

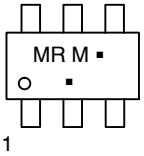
http://onsemi.com

MARKING DIAGRAMS

SC−88/SC−70−6/SOT−363
DF SUFFIX
CASE 419B



TSOP−6
DT SUFFIX
CASE 318G



MR = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

Pin	Function
1	IN A1
2	GND
3	IN A2
4	OUT Y2
5	V_{CC}
6	OUT Y1

FUNCTION TABLE

A Input	$\overline{Y}$ Output
L	L
H	H

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics	Value	Units
V_{CC}	DC Supply Voltage	−0.5 to +7.0	V
V_I	DC Input Voltage	$-0.5 \le V_I \le +7.0$	V
V_O	DC Output Voltage Output in Z or LOW State (Note 1)	$-0.5 \le V_O \le +7.0$	V
I_{IK}	DC Input Diode Current V_I < GND	−50	mA
I_{OK}	DC Output Diode Current V_O < GND	−50	mA
I_O	DC Output Sink Current	±50	mA
I_{CC}	DC Supply Current per Supply Pin	±100	mA
I_{GND}	DC Ground Current per Ground Pin	±100	mA
T_{STG}	Storage Temperature Range	−65 to +150	°C
P_D	Power Dissipation in Still Air SC−88, TSOP−6	 200	mW
θ_{JA}	Thermal Resistance SC−88, TSOP−6	 333	°C/W
T_L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T_J	Junction Temperature Under Bias	+150	°C
V_{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	 > 2000 > 200 N/A	V
$I_{Latchup}$	Latchup Performance Above V_{CC} and Below GND at 85°C (Note 5)	 ±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22−A114−A
3. Tested to EIA/JESD22−A115−A
4. Tested to JESD22−C101−A
5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Units
V_{CC}	Supply Voltage Operating Data Retention Only	 1.65 1.5	 5.5 5.5	V
V_I	Input Voltage	0	5.5	V
V_O	Output Voltage (High or LOW State)	0	5.5	V
T_A	Operating Free−Air Temperature	−55	+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate V_{CC} = 1.8 V ±0.15 V V_{CC} = 2.5 V ±0.2 V V_{CC} = 3.0 V ±0.3 V V_{CC} = 5.0 V ±0.5 V	 0 0 0 0	 20 20 10 5	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		1.65 to 1.95 2.3 to 5.5	0.75 V_{CC} 0.7 V_{CC}			0.75 V_{CC} 0.7 V_{CC}		V
V_{IL}	Low−Level Input Voltage		1.65 to 1.95 2.3 to 5.5			0.25 V_{CC} 0.3 V_{CC}		0.25 V_{CC} 0.3 V_{CC}	V
V_{OH}	High−Level Output Voltage V_{IN} = V_{IH}	I_{OH} = −100 μA	1.65 1.8 2.3 3.0 4.5	1.55 1.7 2.2 2.9 4.4	1.65 1.8 2.3 3.0 4.5		1.55 1.7 2.2 2.9 4.4		V
		I_{OH} = −4 mA I_{OH} = −8 mA I_{OH} = −16 mA I_{OH} = −24 mA I_{OH} = −32 mA	1.65 2.3 3.0 3.0 4.5	1.29 1.9 2.4 2.3 3.8	1.52 2.15 2.80 2.68 4.20		1.29 1.9 2.4 2.3 3.8		V
V_{OL}	Low−Level Output Voltage V_{IN} = V_{IL}	I_{OL} = 100 μA	1.65 1.8 2.3 3.0 4.5		0.0 0.0 0.0 0.0 0.0	0.1 0.1 0.1 0.1 0.1		0.1 0.1 0.1 0.1 0.1	V
		I_{OL} = 4 mA I_{OL} = 8 mA I_{OL} = 16 mA I_{OL} = 24 mA I_{OL} = 32 mA	1.65 2.3 3.0 3.0 4.5		0.08 0.10 0.15 0.22 0.22	0.24 0.30 0.40 0.55 0.55		0.24 0.30 0.40 0.55 0.55	V
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or V_{OUT} = 5.5 V	0			1		10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = 5.5 V or GND	5.5			1		10	μA

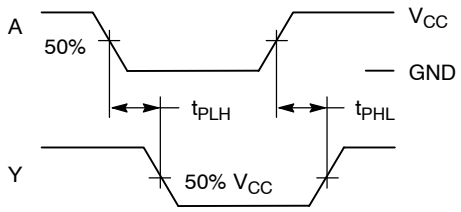
AC ELECTRICAL CHARACTERISTICS $t_R = t_F$ = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay (Figure 3 and 4)	R_L = 1 MΩ, C_L = 15 pF	1.8 ± 0.15	1.8	8.0	9.6	1.8	10.2	ns
		R_L = 1 MΩ, C_L = 15 pF	2.5 ± 0.2	1.0	3.0	5.2	1.0	5.8	
		R_L = 1 MΩ, C_L = 15 pF	3.3 ± 0.3	0.8	2.3	3.6	0.8	4.0	
		R_L = 500 Ω, C_L = 50 pF		1.2	3.0	4.6	1.2	5.1	
		R_L = 1 MΩ, C_L = 15 pF	5.0 ± 0.5	0.5	1.8	2.9	0.5	3.2	
		R_L = 500 Ω, C_L = 50 pF		0.8	2.4	3.8	0.8	4.2	

CAPACITIVE CHARACTERISTICS

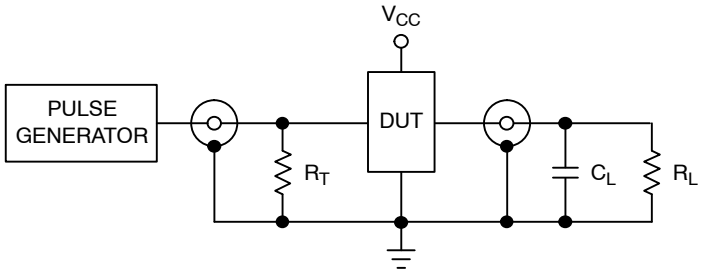
Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	7.0	pF
C_{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	9 11	pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



PROPAGATION DELAYS
$t_R = t_F$ = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

Figure 3. Switching Waveforms



R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

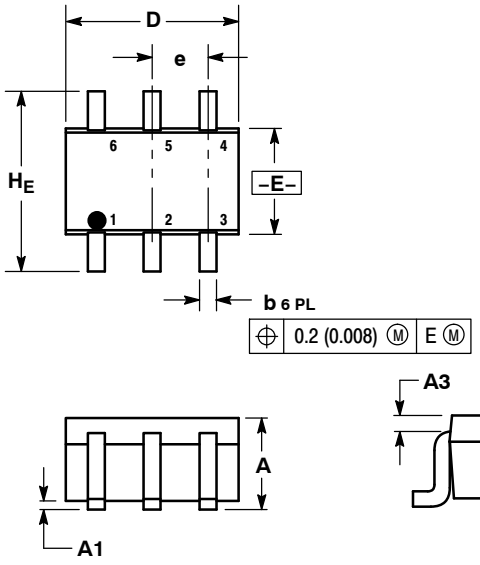
ORDERING INFORMATION

Device	Package	Shipping†
NL27WZ16DFT2G	SC−88/SC−70/SOT−363 (Pb−Free)	3000 /Tape & Reel
NLV27WZ16DFT2G*	SC−88/SC−70/SOT−363 (Pb−Free)	3000 /Tape & Reel
NL27WZ16DTT1G	TSOP−6 (Pb−Free)	3000 /Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

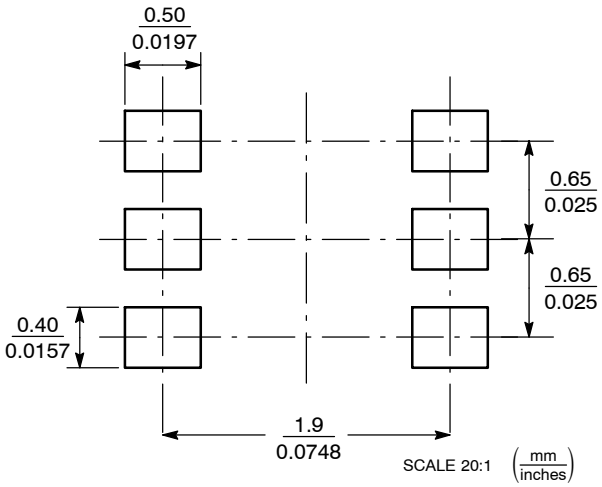
SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE W



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B−01 OBSOLETE, NEW STANDARD 419B−02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	2.00	2.10	2.20	0.078	0.082	0.086

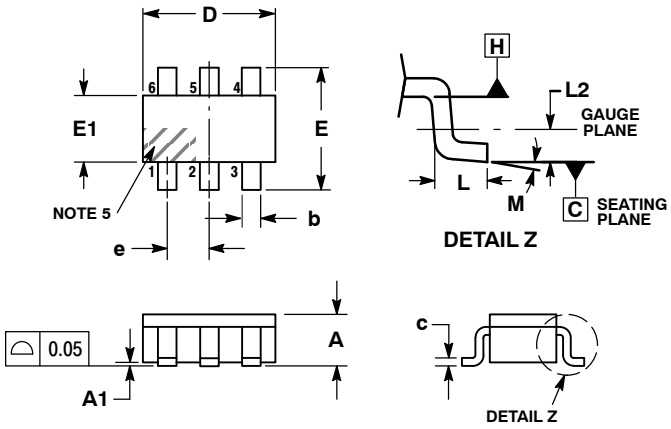
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

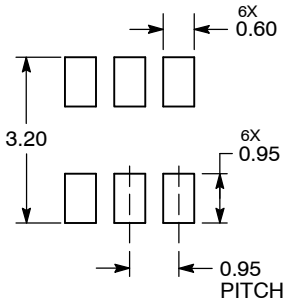
TSOP−6
CASE 318G−02
ISSUE U



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2		0.25 BSC	
M	0°	–	10°

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
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Phone: 421 33 790 2910
Japan Customer Focus Center
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ON Semiconductor Website: **www.onsemi.com**

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